

Features

- Super Low Gate Charge
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

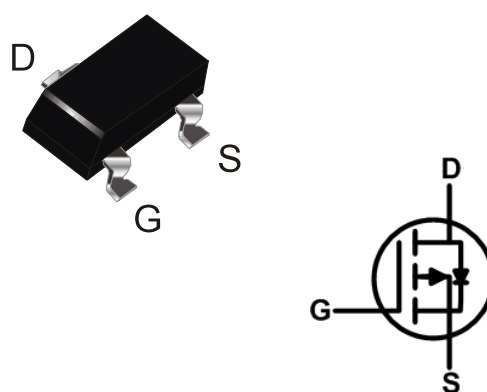
BVDSS	RDSON	ID
-20V	45mΩ	-4.9A

Description

The JHT2611 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The JHT2611 meet the RoHS and Green Product requirement with full function reliability approved.

SOT 23 Pin Configurations



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.9	A
I_{DM}	Pulsed Drain Current ²	-14	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.31	W
$P_D@T_A=70^\circ C$	Total Power Dissipation ³	0.84	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	120	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	95	$^\circ C/W$

JHT2611

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.014	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5V, I_D=-4.9A$	---	40	45	m Ω
		$V_{GS}=-2.5V, I_D=-3.4A$	---	50	60	
		$V_{GS}=-1.8V, I_D=-2A$	---	65	85	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.4	---	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.95	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-3A$	---	12.8	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-3A$	---	10.2	14.3	nC
Q_{gs}	Gate-Source Charge		---	1.89	2.6	
Q_{gd}	Gate-Drain Charge		---	3.1	4.3	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=3.3\Omega, I_D=-3A$	---	5.6	11.2	ns
T_r	Rise Time		---	40.8	73	
$T_{d(off)}$	Turn-Off Delay Time		---	33.6	67	
T_f	Fall Time		---	18	36	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	857	1200	pF
C_{oss}	Output Capacitance		---	114	160	
C_{rss}	Reverse Transfer Capacitance		---	108	151	
Diode Characteristics						
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V, \text{Force Current}$	---	---	-4.9	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-14	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-3A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	21.8	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	6.9	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

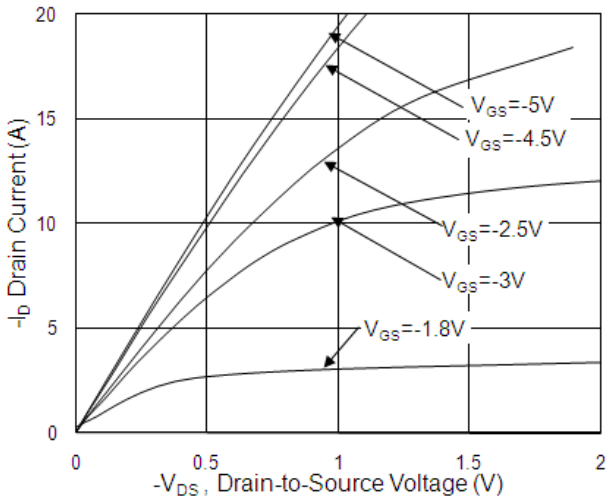


Fig.1 Typical Output Characteristics

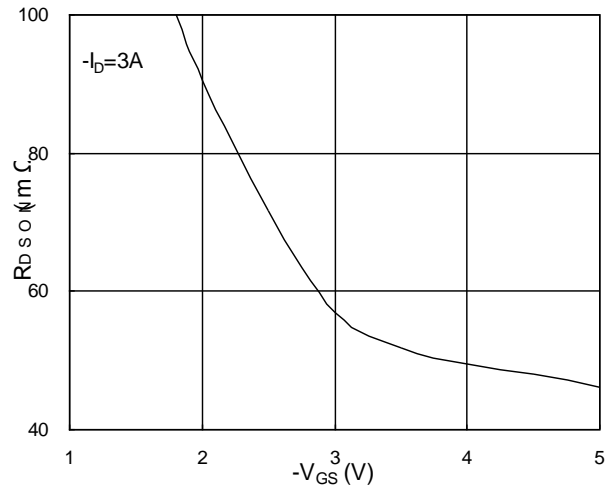


Fig.2 On-Resistance vs. G-S Voltage

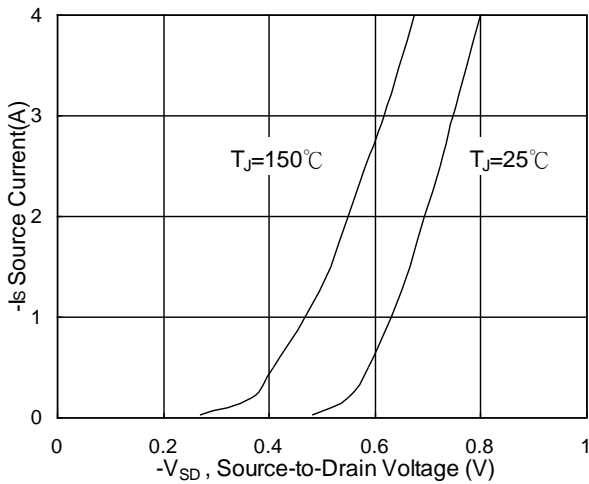


Fig.3 Forward Characteristics of Reverse

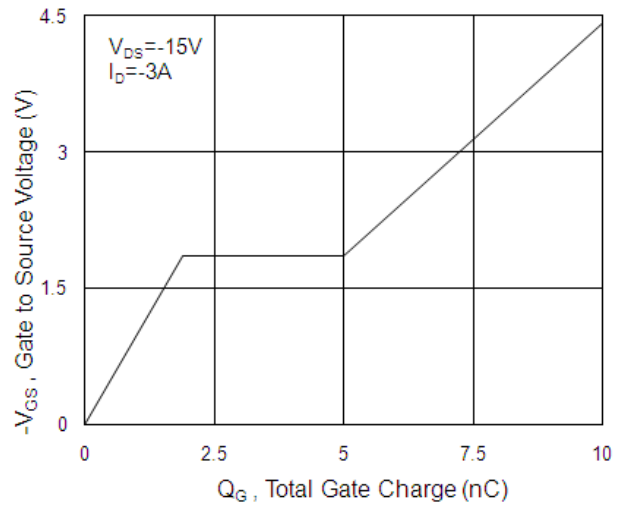


Fig.4 Gate-charge Characteristics

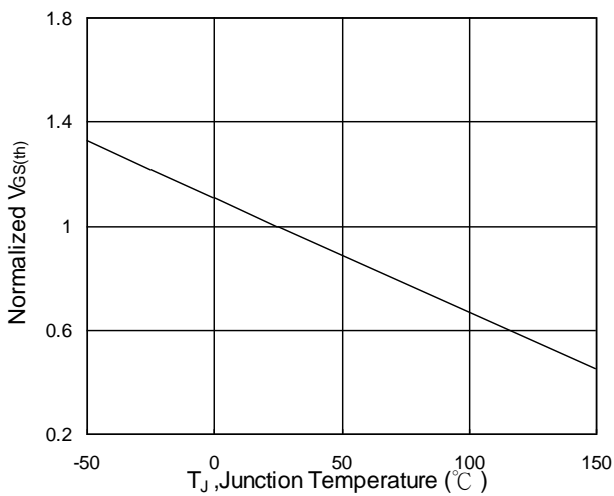


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

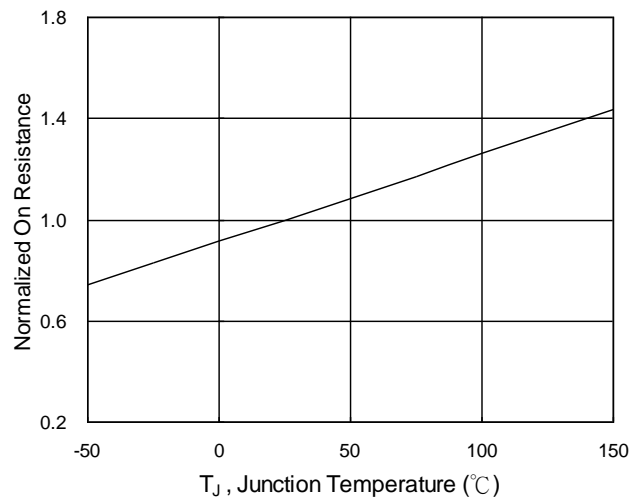


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

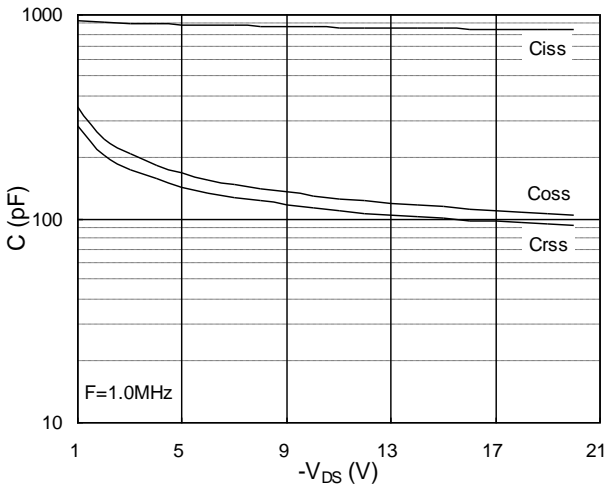


Fig.7 Capacitance

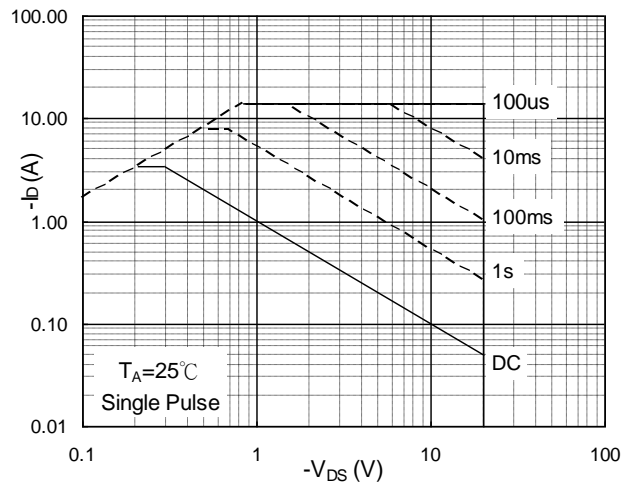


Fig.8 Safe Operating Area

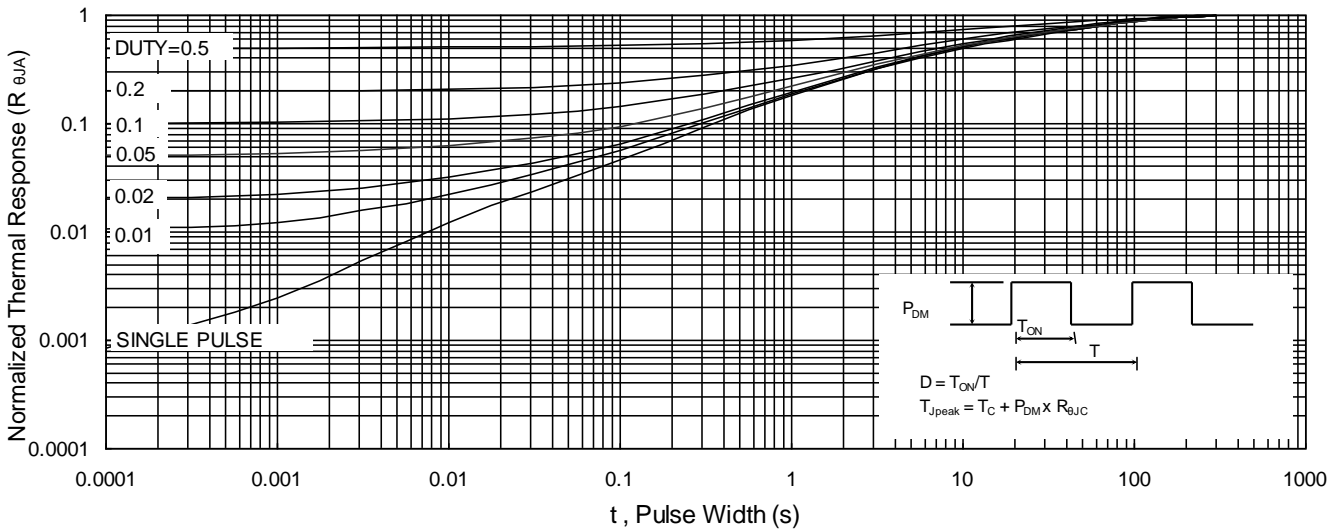


Fig.9 Normalized Maximum Transient Thermal Impedance

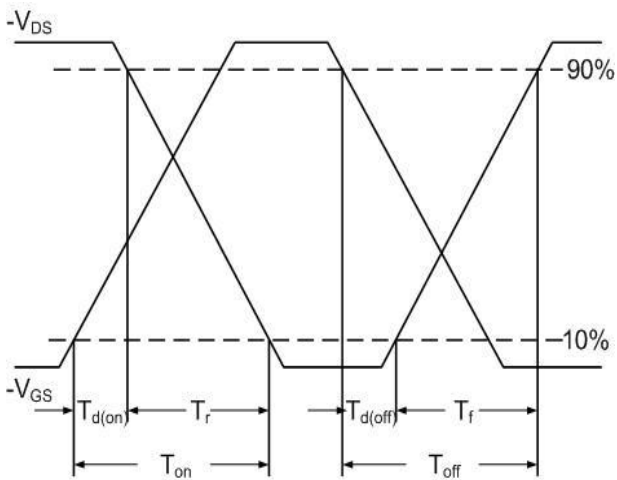


Fig.10 Switching Time Waveform

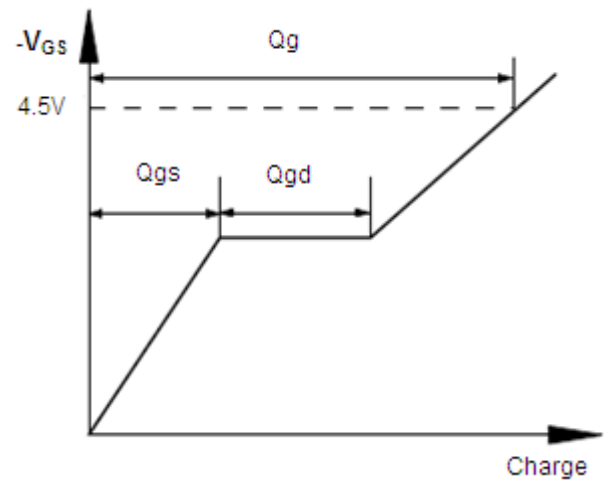
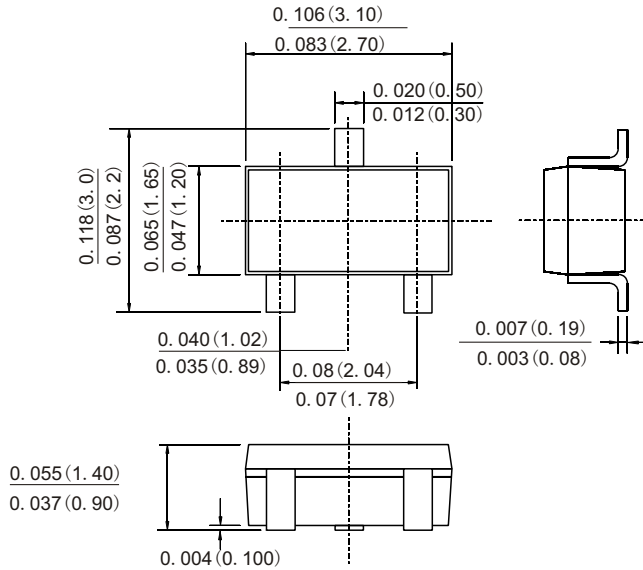


Fig.11 Gate Charge Waveform

JHT2611

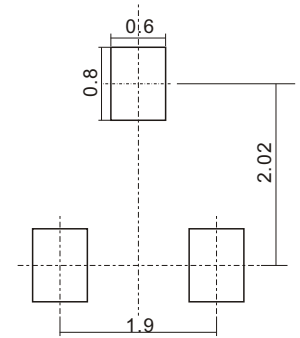
PACKAGE OUTLINE DIMENSIONS

SOT-23



Dimensions in inches and (millimeters)

Suggested Pad Layout



Dimensions in millimeters

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